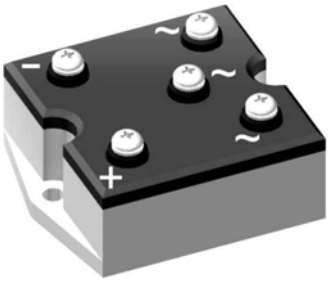
Standard Rectifier Module

3~ Rectifier		
V_{RRM}	=	1800 V
I_{DAV}	=	35 A
I_{FSM}	=	400 A

3~ Rectifier Bridge

Part number

VUO35-18NO7



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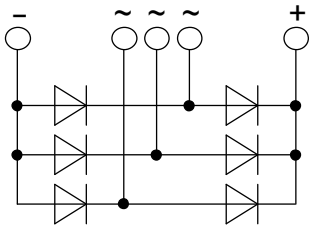


Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

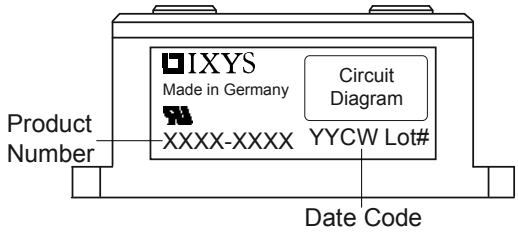
- Diode for main rectification
- For three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: PWS-A

- Industry standard outline
- RoHS compliant
- Easy to mount with two screws
- Base plate: Aluminium internally DCB isolated
- Advanced power cycling

Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	*max. non-repetitive reverse blocking voltage*		T_{VJ} = 25°C			1900	V
V_{RRM}	*max. repetitive reverse blocking voltage*		T_{VJ} = 25°C			1800	V
I_R	*reverse current*	V_R = 1800 V	T_{VJ} = 25°C			40	µA
		V_R = 1800 V	T_{VJ} = 150°C			1.5	mA
V_F	*forward voltage drop*	I_F = 15 A	T_{VJ} = 25°C			1.10	V
		I_F = 45 A				1.38	V
		I_F = 15 A	T_{VJ} = 125 °C			1.01	V
		I_F = 45 A				1.38	V
I_{DAV}	*bridge output current*	T_C = 85°C	T_{VJ} = 150°C			35	A
		rectangular d = ⅓					
V_{F0}	*threshold voltage* } *for power loss calculation only*		T_{VJ} = 150°C			0.80	V
r_F	*slope resistance* }					12.9	mΩ
R_{thJC}	*thermal resistance junction to case*					4.2	K/W
R_{thCH}	*thermal resistance case to heatsink*				0.6		K/W
P_{tot}	*total power dissipation*		T_C = 25°C			29	W
I_{FSM}	*max. forward surge current*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			400	A
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			430	A
		t = 10 ms; (50 Hz), sine	T_{VJ} = 150°C			340	A
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			365	A
I^2t	*value for fusing*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			800	A²s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			770	A²s
		t = 10 ms; (50 Hz), sine	T_{VJ} = 150°C			580	A²s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			555	A²s
C_J	*junction capacitance*	V_R = 400 V; f = 1 MHz	T_{VJ} = 25°C		10		pF

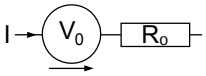
Package PWS-A				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I_{RMS}	*RMS current*	per terminal				100	A
T_{stg}	*storage temperature*			-40		125	°C
T_{VJ}	*virtual junction temperature*			-40		150	°C
Weight					100		g
M_D	*mounting torque*			1.25		1.75	Nm
M_T	*terminal torque*			1.25		1.75	Nm
$d_{Spp/App}$	*creepage distance on surface | striking distance through air*		*terminal to terminal*	6.5			mm
$d_{Spb/Apb}$			*terminal to backside*	8.5			mm
V_{ISOL}	*isolation voltage*	t = 1 second	50/60 Hz, RMS; I_{ISOL} ≤ 1 mA	3000			V
		t = 1 minute		2500			V



Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VUO35-18NO7	VUO35-18NO7	Box	20	456667

Equivalent Circuits for Simulation

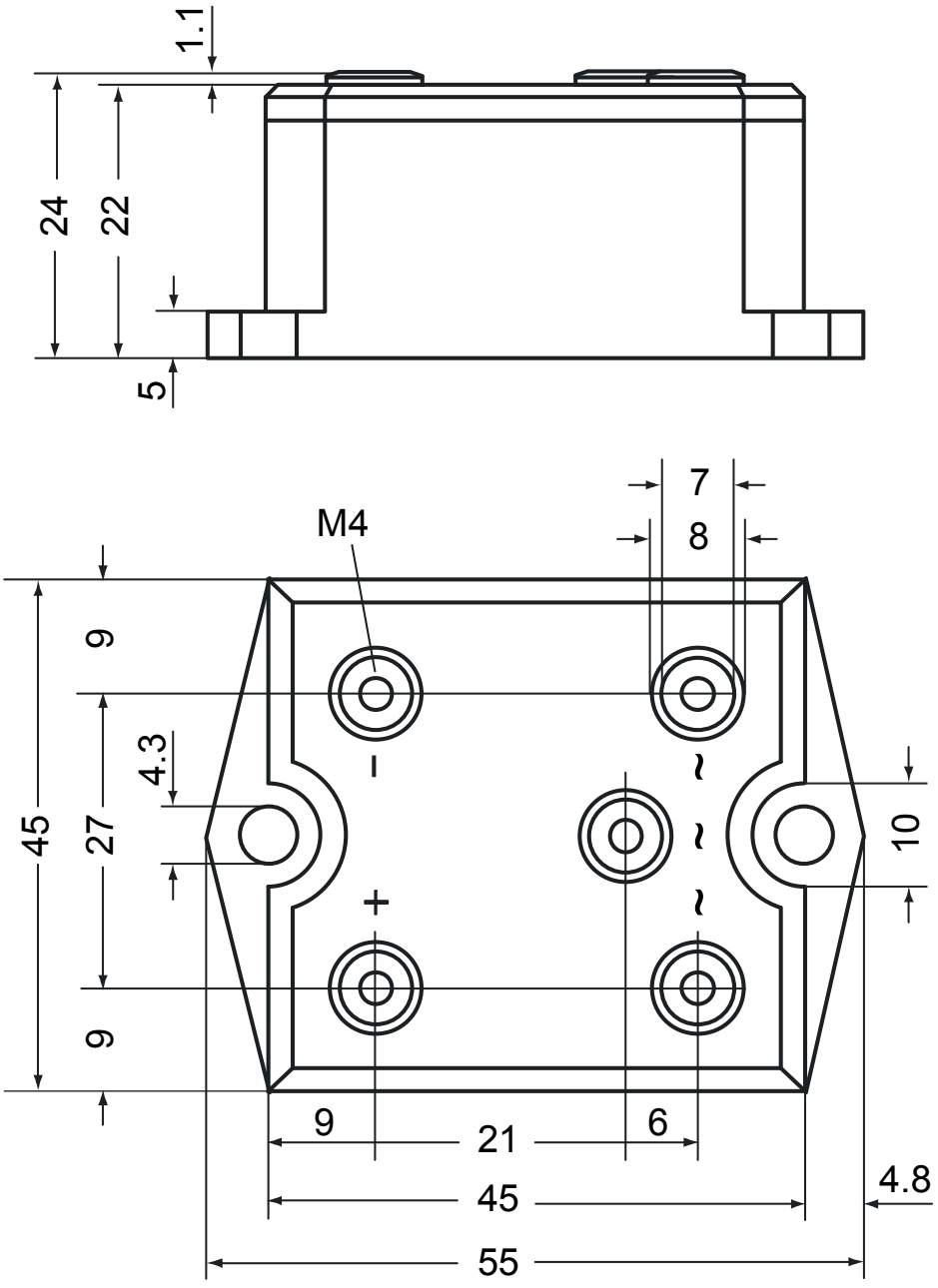
** on die level* T_{VJ} = 150 °C



Rectifier

$V_{0\,max}$	*threshold voltage*	0.8	V
$R_{0\,max}$	*slope resistance **	11.7	mΩ

Outlines PWS-A



Rectifier

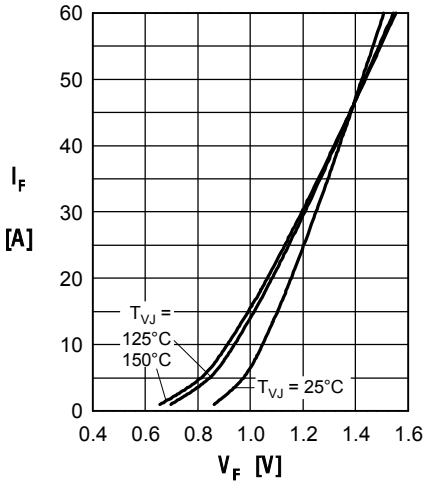


Fig. 1 Forward current vs. voltage drop per diode

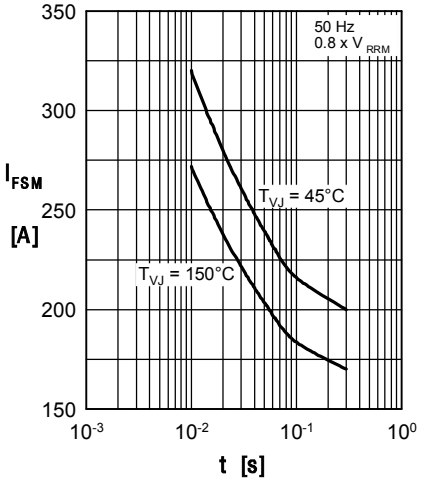


Fig. 2 Surge overload current vs. time per diode

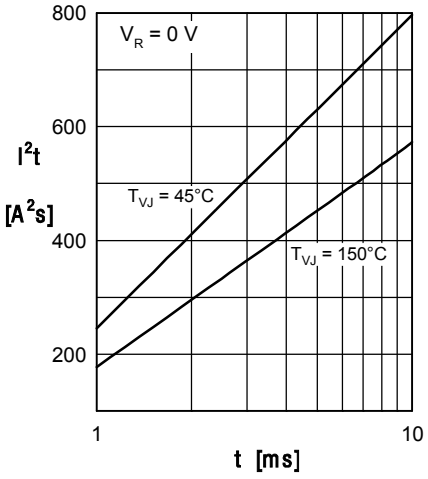


Fig. 3 I^2t vs. time per diode

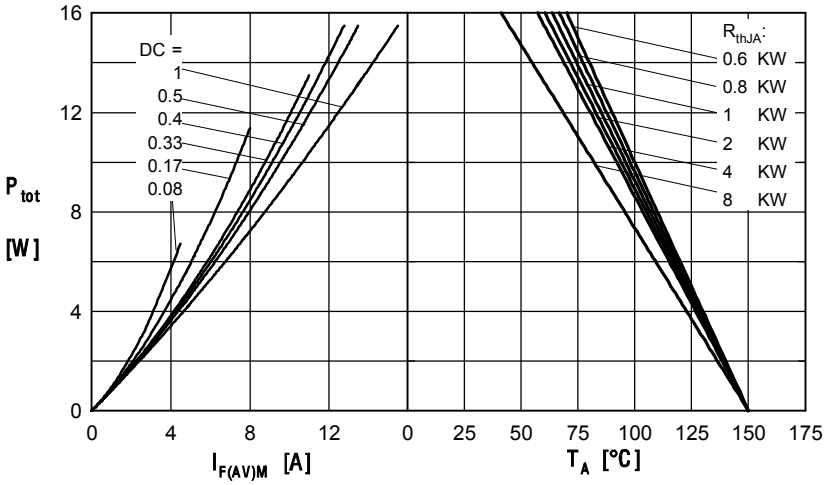


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

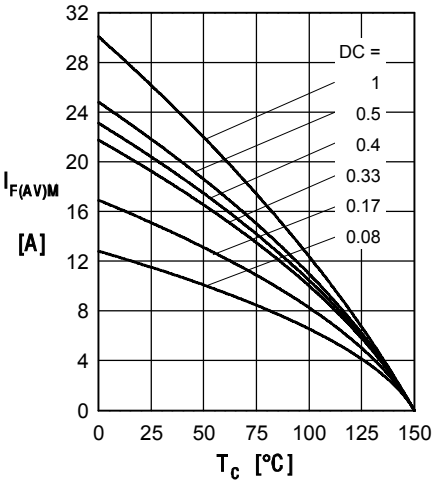


Fig. 5 Max. forward current vs. case temperature per diode

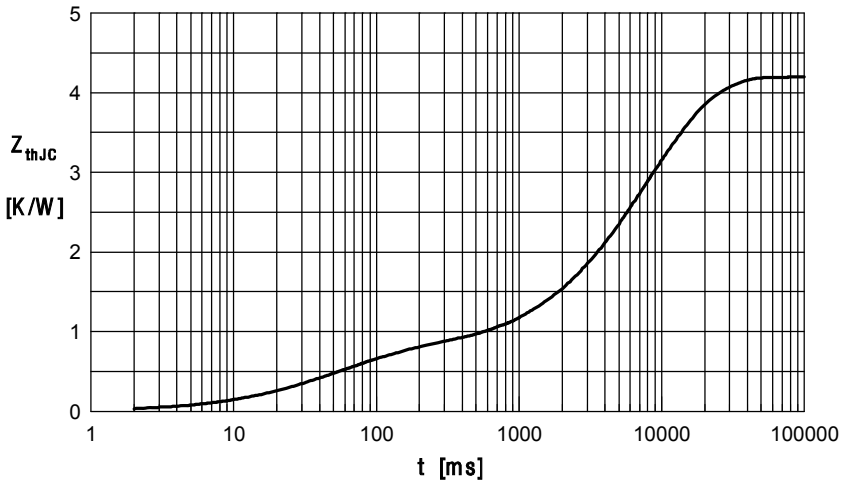


Fig. 6 Transient thermal impedance junction to case vs. time per diode

Constants for Z_{thJC} calculation:

i	R_{th} (K/W)	t_i (s)
1	0.194	0.024
2	0.556	0.070
3	0.450	3.250
4	3.000	9.300